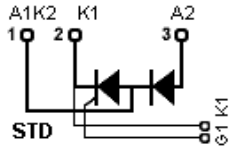


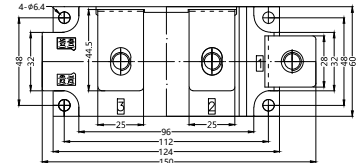
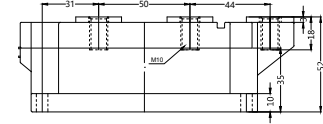
STD240GK42BT

Thyristor-Diode Modules



Type	V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V
STD240GK30BT	3400	3000
STD240GK32BT	3600	3200
STD240GK34BT	3800	3400
STD240GK36BT	4000	3600
STD240GK38BT	4200	3800
STD240GK40BT	4400	4000
STD240GK42BT	4600	4200

Dimensions in mm (1mm=0.0394")



Symbol	Test Conditions		Maximum Ratings	Unit
I_{TRMS}, I_{FRMS} I_{TAVM}, I_{FAVM}	$T_V = T_{VJM}$ $T_C = 85^\circ C; 180^\circ$ sine		377 240	A
I_{TSM}, I_{FSM}	$T_V = 45^\circ C$ $V_R = 0$	$t = 10ms$ (50Hz), sine $t = 8.3ms$ (60Hz), sine	9000 10900	A
	$T_V = T_{VJM}$ $V_R = 0$	$t = 10ms$ (50Hz), sine $t = 8.3ms$ (60Hz), sine	8000 9600	
$\int i^2 dt$	$T_V = 45^\circ C$ $V_R = 0$	$t = 10ms$ (50Hz), sine $t = 8.3ms$ (60Hz), sine	470000 565000	A^2s
	$T_V = T_{VJM}$ $V_R = 0$	$t = 10ms$ (50Hz), sine $t = 8.3ms$ (60Hz), sine	414000 496000	
$(di/dt)_{cr}$	$T_V = T_{VJM}$ $f = 50Hz, t_p = 200\mu s$ $V_D = 2/3 V_{DRM}, I_G = 1A$ $di/dt = 1A/\mu s$	repetitive	150	A/ μs
		non repetitive, $I_T = I_{TAVM}$	500	
$(dv/dt)_{cr}$	$T_V = T_{VJM};$ $R_{GK} = \infty$; method 1 (linear voltage rise)	$V_{DR} = 2/3 V_{DRM}$	1000	V/ μs
P_{GM}	$T_V = T_{VJM}$ $I_T = I_{TAVM}$	$t_p = 30\mu s$ $t_p = 500\mu s$	120 60	W
P_{GAV}			8	W
V_{RGM}			10	V
T_V T_{VJM} T_{stg}			-40...+140 140 -40...+125	$^\circ C$
V_{ISOL}	50/60Hz, RMS $I_{ISOL} \leq 1mA$	$t = 1min$ $t = 1s$	3000 3600	V~
M_d	Mounting torque (M6) Terminal connection torque (M10)		4.5-7/40-60 11-13/97-115	Nm/lb.in.
Weight	Typical		1500	g

Sirectifier®

STD240GK42BT

Thyristor-Diode Modules

Symbol	Test Conditions	Characteristic Values	Unit
I_{RRM}	$T_{VJ}=T_{VJM}; V_R=V_{RRM}$	50	mA
V_{TM}	$I_{TM}=720A; T_{VJ}=25^{\circ}C$	3.50	V
V_{TO}	For power-loss calculations only ($T_{VJ}=T_{VJM}$)	1.560	V
r_T		2.14	m Ω
V_{GT}	$V_D=6V; T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	3 4	V
I_{GT}	$V_D=6V; T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	200 300	mA
V_{GD}	$T_{VJ}=T_{VJM}; V_D=2/3V_{DRM}$	0.25	V
I_{GD}	$T_{VJ}=T_{VJM}; V_D=2/3V_{DRM}$	10	mA
I_L	$T_{VJ}=25^{\circ}C; t_p=30\mu s; V_D=6V$ $I_G=1A; di_G/dt=1A/\mu s$	400	mA
I_H	$T_{VJ}=25^{\circ}C; V_D=6V; R_{GK}=\infty$	300	mA
t_{gd}	$T_{VJ}=25^{\circ}C; V_D=1/2V_{DRM}$ $I_G=1A; di_G/dt=1A/\mu s$	2	μs
t_q	$T_{VJ}=T_{VJM}; I_T=240A; t_p=200\mu s; -di/dt=10A/\mu s$ $V_R=100V; dv/dt=50V/\mu s; V_D=2/3V_{DRM}$ typ.	250	μs
R_{thJC}	DC current	0.0320	K/W
R_{thJK}	DC current	0.048	K/W
d_s	Creeping distance on surface	12.7	mm
d_A	Creepage distance in air	9.6	mm
a	Maximum allowable acceleration	50	m/s ²

FEATURES

- * International standard package
- * Copper base plate
- * Pressure Contact Technology
- * BusBar Terminal
- * Isolation voltage 3600 V~
- * RoHS compliant

APPLICATIONS

- * Motor control, softstarter
- * Power converter
- * Heat and temperature control for industrial furnaces and chemical processes
- * Lighting control
- * Solid state switches

ADVANTAGES

- * Simple mounting
- * Improved temperature and power cycling
- * Reduced protection circuits



STD240GK42BT

Thyristor-Diode Modules

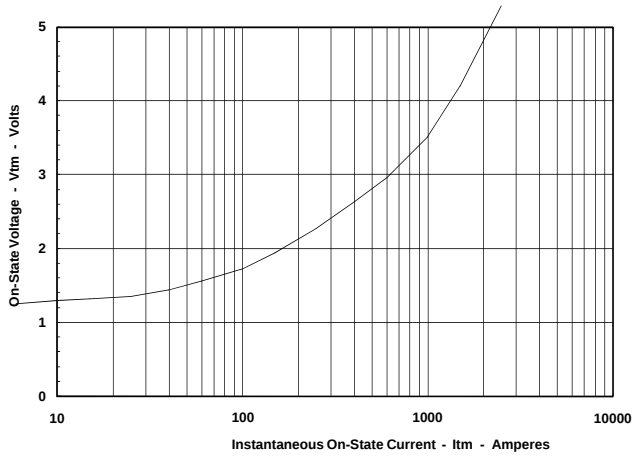


Fig.1 Maximum On-State Forward Voltage Drop ($T_j = 125^\circ\text{C}$)

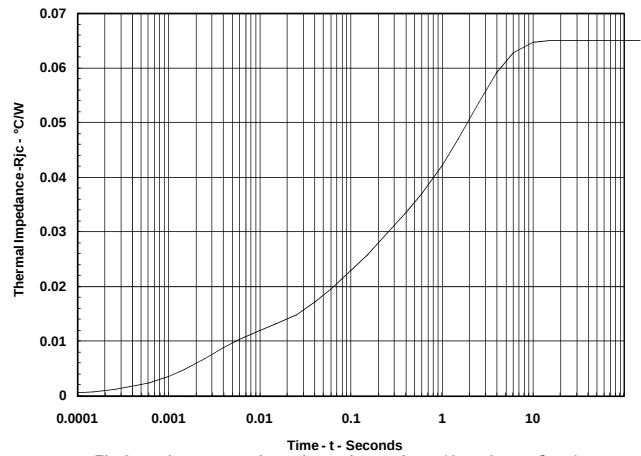


Fig.2 Maximum Transient Thermal Impedance (Junction to Case)

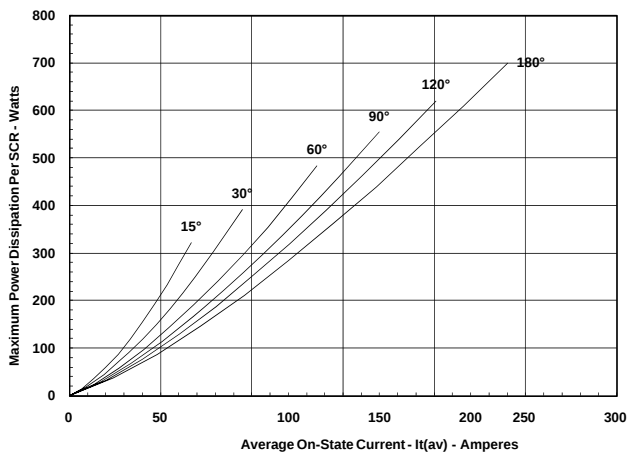


Fig.3 Maximum On-State Power Dissipation (Sinusoidal Waveform)

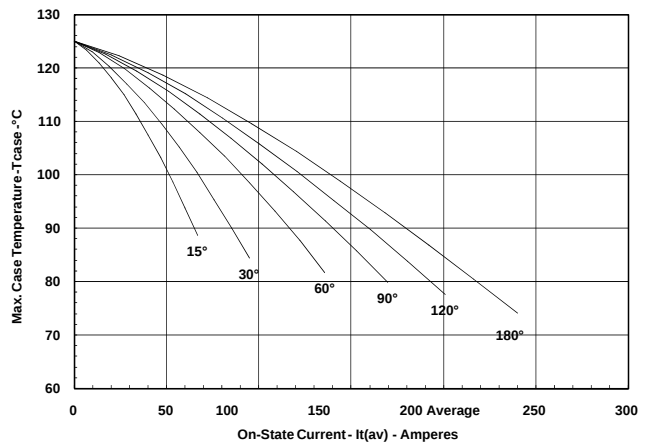


Fig.4 Maximum Allowable Case Temperature (Sinusoidal Waveform)

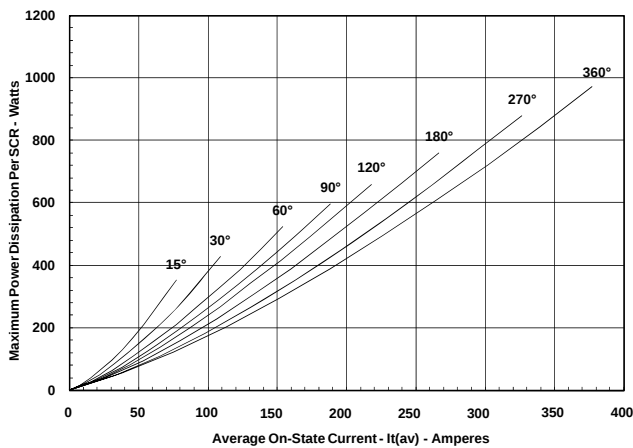


Fig.5 Maximum On-State Power Dissipation (Rectangular Waveform)

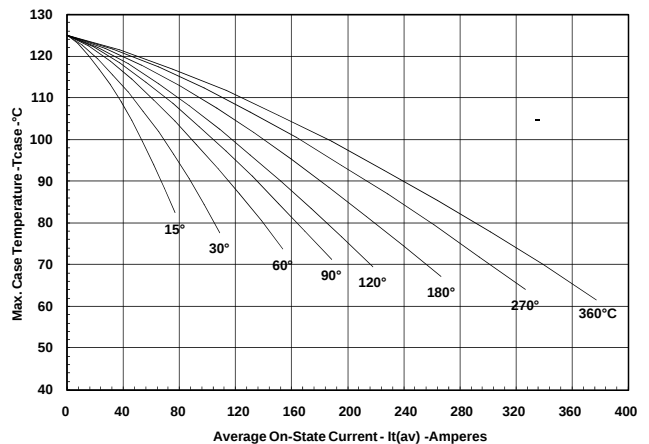


Fig.6 Maximum Allowable Case Temperature (Rectangular Waveform)